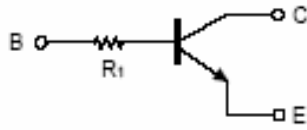




PNP Transistors

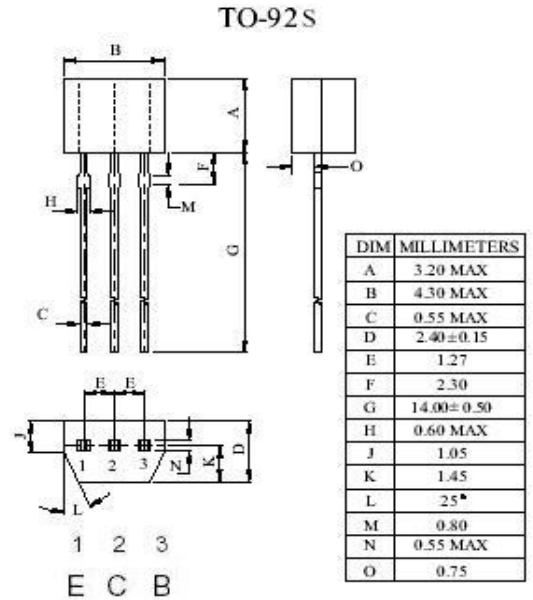
—NPN Silicon—

■ ■ **APPLICATION:** Interface Circuit and Driver Circuit Applications.



■ ■ **MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Breakdown Voltage	V_{CBO}	50	V
Collector-Emitter Breakdown Voltage	V_{CEO}	50	V
Emitter-Base Breakdown Voltage	V_{EBO}	5	V
Collector Current	I_C	0.1	A
Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



■ ■ **ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector-Base Breakdown Voltage	BV_{CBO}	50			V	$I_C=50\mu A$ $I_E=0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	50			V	$I_C=1mA$ $I_B=0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	$I_E=50\mu A$ $I_C=0$
Collector Cut-off Current	I_{CBO}			0.5	μA	$V_{CB}=50V$ $I_E=0$
Emitter Cut-off Current	I_{EBO}			0.5	μA	$V_{EB}=4V$ $I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	$I_C=10mA$ $I_B=1mA$
DC Current Gain	h_{FE}	100	300	600	β	$V_{CE}=5V$ $I_C=1mA$
Input Resistance	R_1	3	10	13	K Ω	
Gain bandwidth product	f_T		250		MHZ	$V_{CE}=10V$ $I_E=-5mA$ $f=100MHz$

■ ■ h_{FE} Classification And Marking

Print Mark C114TS

Classification

h_{FE} 100-600